


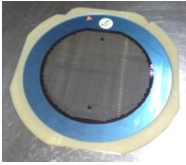





DEVICE TYPE: 100V Trench Sky datasheet

CHIP LAY-OUT	CHIP INFO	DIMENSION / DATA		
 <p>TOP VIEW</p>  <p>SIDE VIEW</p>	$V_{RWM}$	100V		
	$I_{FAV}$	3A~15A		
	$T_{JMAX}$	150°C		
	WAFER SIZE	150 ± 0.3 mm		
	CHIP SIZE	58mil~94mil		
	CHIP THICKNESS	10 mils		
	SCRIBE LINE WIDTH	4 mils		
	<b>METALLIZATION</b>			
	<b>- Top Metal</b>			
		Ag	7um	
	Al	7.2um		
<b>- Back Metal</b>				
	Ag	1.7um		
<b>ESD Capability</b>	Minimum Electro-Static Discharge resistance to voltage			
	JEDEC Standard	>8	kv	
	IEC-61000-4-2 Standard	>8		
<b>Delivery</b>	Wafer (6 inch)	Dies with tape	Dies in bottle (≤70ml)	
				

YIELD CUT-OFF: 95%

WAFER MANUFACTURER: Li-ON Microelectronics

LOCATION: Hangzhou, China

Update:2019-8-24



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<b>ELECTRICAL RATINGS &amp; CHARACTERISTICS</b> $T_J > 150^\circ\text{C}$ ( $T_A = 25^\circ\text{C}$ , UNLESS OTHERWISE NOTED)								
<b>SYMBOL</b>	<b>CHIP SIZE (mil)</b>	<b>CONTACT SIZE(mil)</b>	<b>I<sub>FAV</sub> (A)</b>	<b>Device</b>	<b>RS(A)</b>	<b>IFSM(A)</b>	<b>V<sub>FMAX</sub>(V)</b>	<b>I<sub>RMAX</sub>(uA)</b>
Single die	58	48	3	TS6039A	0.5	80	0.6	30
	72	65	5	TS4058A	0.5	120	0.6	25
	75	65	5	TS4051A	0.5	120	0.6	25
	82	72	10	TS4036A	0.5	200	0.7	30
	94	84	15	TS4047A	0.5	275	0.72	50